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This application was filed on 15 - 09 - 2003 as a
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(54) **Optical recording method and medium.**

(57) The present invention relates to an optical recording method for recording mark length modulated information with a plurality of recording mark lengths by irradiating a recording medium with a light, the optical recording method comprising a reduced number of divisions in the pulse division scheme.

Preferred phase change mediums are those having a recording layer containing excessive Sb in the SbTe eutectic composition. A particularly preferred composi-

tion contains excessive Sb and also Ge in the base $\text{Sb}_{70}\text{Te}_{30}$ eutectic composition. The Sb/Te ratio is particularly preferably set to 4 or more. The content of Ge is preferably 10 atomic % or less. An example of such a recording layer is a $\text{M}_z\text{Ge}_y(\text{Sb}_x\text{Te}_{1-x})_{1-y-z}$ alloy (where $0 \leq z \leq 0.1$, $0 < y \leq 0.3$, $0.8 \leq x$; and M is at least one of In, Ga, Si, Sn, Pb, Pd, Pt, Zn, Au, Ag, Zr, Hf, V, Nb, Ta, Cr, Co, Mo, Mn, Bi, O, N and S).

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